

STRUCTURE FOR RADIOFREQUENCY APPLICATIONS

Abstract

The invention relates to a structure (1) for radiofrequency applications which includes: a semiconducting supporting substrate (2); a trapping layer (3) arranged on the supporting substrate (2); the trapping layer (3) being characterised in that it includes a higher defect density than a predetermined defect density; the predetermined defect density is the defect density beyond which the electric resistivity of the trapping layer (3) is no lower than 10 Kohm.cm over a temperature range of $[-20\text{ }^{\circ}\text{C}; +120\text{ }^{\circ}\text{C}]$.

Fig. 1